

isc Silicon PNP Power Transistor

2SB681

DESCRIPTION

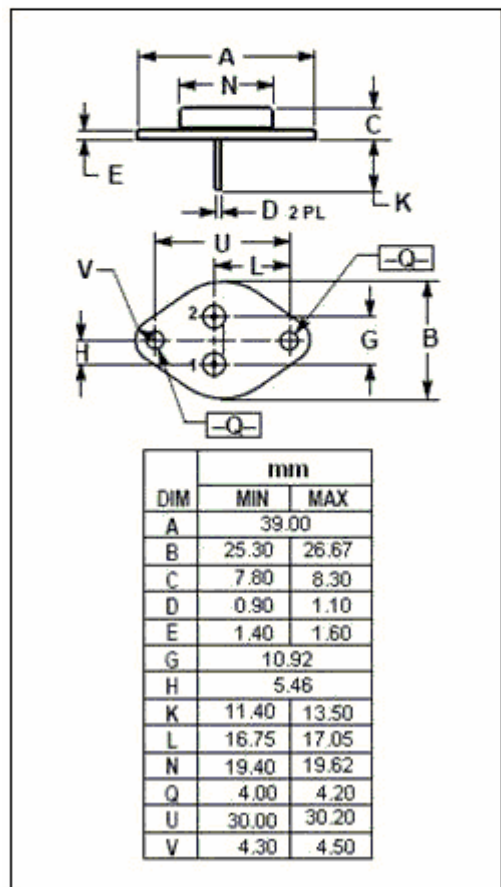
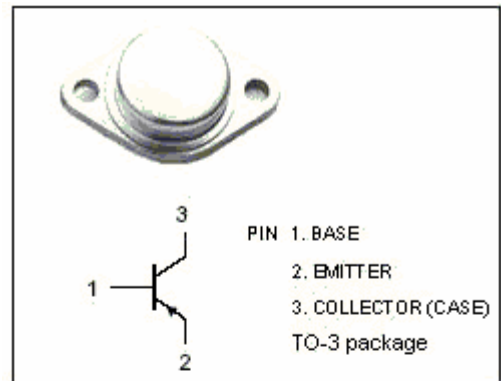
- High Current Capability
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min.})$

APPLICATIONS

- For AF power amplifier use.
- Recommended for use in output stage of 80 watts power amplifier .

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA ; I _B = 0	-150			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -6A; I _B = -0.6A			-2.5	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -120V; I _B = 0			-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -1A ; V _{CE} = -5V	40		140	
h _{FE-2}	DC Current Gain	I _C = -5A ; V _{CE} = -5V	20			
f _T	Current-Gain—Bandwidth Product	I _C = -1A ; V _{CE} = -5V		13		MHz